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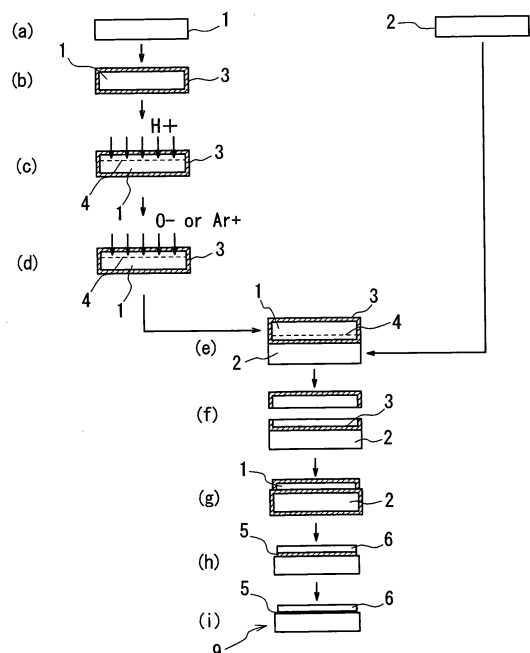
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(54) **Method of producing semiconductor substrate**

(57) There is provided a method for suppressing the occurrence of defects such as voids or blisters even in the laminated wafer having an oxide film of a thickness thinner than the conventional one, wherein hydrogen ions are implanted into a wafer for active layer having an oxide film of not more than 50 nm in thickness to form a hydrogen ion implanted layer, and ions other than hydrogen are implanted up to a position that a depth from the surface side the hydrogen ion implantation is shallower than the hydrogen ion implanted layer, and the wafer for active layer is laminated onto a wafer for support substrate through the oxide film, and then the wafer for active layer is exfoliated at the hydrogen ion implanted layer.

FIG. 3





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The present search report has been drawn up for all claims			
Place of search		Date of completion of the search	Examiner
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<p>CATEGORY OF CITED DOCUMENTS</p> <p>X : particularly relevant if taken alone Y : particularly relevant if combined with another document of the same category A : technological background O : non-written disclosure P : intermediate document</p> <p>T : theory or principle underlying the invention E : earlier patent document, but published on, or after the filing date D : document cited in the application L : document cited for other reasons & : member of the same patent family, corresponding document</p>			

3
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**ANNEX TO THE EUROPEAN SEARCH REPORT
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This annex lists the patent family members relating to the patent documents cited in the above-mentioned European search report. The members are as contained in the European Patent Office EDP file on The European Patent Office is in no way liable for these particulars which are merely given for the purpose of information.

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